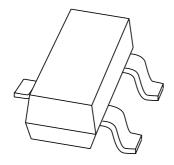
DISCRETE SEMICONDUCTORS

DATA SHEET



BCW89 PNP general purpose transistor

Product data sheet Supersedes data of 1997 Mar 11 1999 Apr 15



PNP general purpose transistor

BCW89

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 60 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.

MARKING

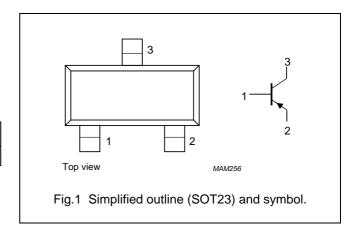
TYPE NUMBER	MARKING CODE(1)			
BCW89	H3*			

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-80	V
V_{CEO}	collector-emitter voltage	open base; I _C = −2 mA	_	-60	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

1999 Apr 15 2

PNP general purpose transistor

BCW89

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -20 \text{ V}$	_	_	-100	nA
		$I_E = 0$; $V_{CB} = -20 \text{ V}$; $T_j = 100 \text{ °C}$	_	_	-10	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -10 \mu A; V_{CE} = -5 V$	_	90	_	
		$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	120	=	260	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-80	-300	mV
		$I_C = -50 \text{ mA}; I_B = -2.5 \text{ mA}$	_	-150	_	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-720	=	mV
		$I_C = -50 \text{ mA}; I_B = -2.5 \text{ mA}$	_	-810	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	_	-750	mV
C _c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 \text{ V}; f = 1 \text{ MHz}$	_	4.5	=	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	_	150	-	MHz
F	noise figure	$\begin{split} I_C &= -200 \; \mu\text{A}; \; V_{CE} = -5 \; V; \; R_S = 2 \; k\Omega; \\ f &= 1 \; k\text{Hz}; \; B = 200 \; \text{Hz} \end{split}$	_	_	10	dB

1999 Apr 15 3

PNP general purpose transistor

BCW89

PACKAGE OUTLINE

UNIT

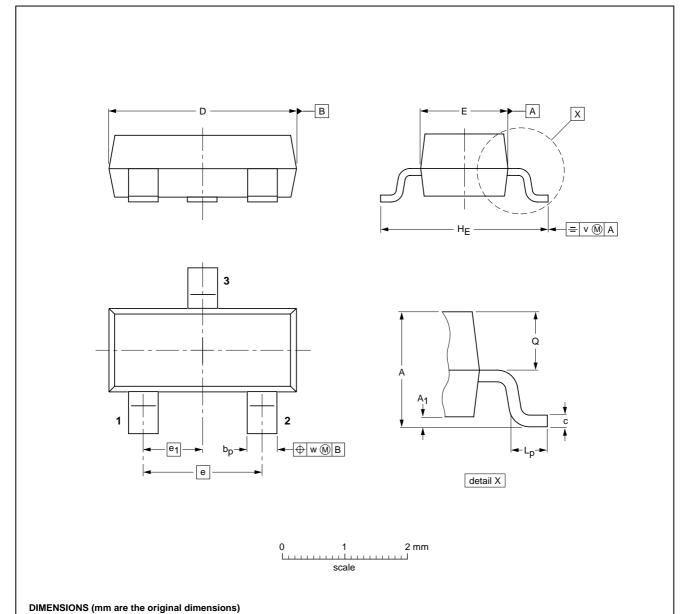
mm

1.1

0.9

Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				-97-02-28 99-09-13	

 H_{E}

2.5 2.1 L_{p}

0.45 0.15

Ε

1.4 1.2

3.0 2.8

0.15

0.09

е

Q

0.55 0.45 w

0.1

1999 Apr 15 4

0.48 0.38

0.1

PNP general purpose transistor

BCW89

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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1999 Apr 15 5

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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